

WHAT IS CLAIMED IS:

1. A liquid phase growth method comprising the

steps of:

5 immersing a substrate in a crucible that stores a solvent having a growth material dissolved therein; and  
cooling the solvent from an interior thereof.

2. The liquid phase growth method according to  
Claim 1, wherein the solvent is cooled from a central  
10 part thereof.

3. The liquid phase growth method according to  
Claim 1, wherein the cooling step is carried out by  
letting a medium flow through a tube immersed in the  
15 crucible.

4. The liquid phase growth method according to  
Claim 1, wherein the cooling step is carried out by  
letting a medium flow through a hole formed in a jig  
20 for holding the substrate.

5. The liquid phase growth method according to  
Claim 1, wherein the cooling step is carried out by  
letting a medium flow through a hole formed in the  
25 crucible.

6. The liquid phase growth method according to

Claim 3, wherein the medium is a gas.

7. The liquid phase growth method according to  
Claim 1, wherein a liquid phase growth bath for  
5 formation of a p<sup>+</sup> type Si layer is used as the crucible  
and, subsequent thereto, a liquid phase growth bath for  
formation of an n<sup>-</sup> type Si layer is used as the  
crucible.

10 8. The liquid phase growth method according to  
Claim 1, wherein the growth material is Si, Ge, or  
GaAs.

9. The liquid phase growth method according to  
15 Claim 1, wherein the solvent is a melt of In or Sn.

10. A liquid phase growth apparatus comprising:  
a crucible for storing a solvent having a growth  
material dissolved therein;  
20 a wafer cassette for holding a substrate to be  
immersed in the solvent; and  
a cooling section for cooling the solvent from an  
interior thereof.

25 11. The liquid phase growth apparatus according  
to Claim 10, wherein the cooling section is a tube  
which is immersed in the crucible and through which a

medium is made to flow.

12. The liquid phase growth apparatus according  
to Claim 10, wherein the cooling section is a hole  
5 which is formed inside the wafer cassette and through  
which a medium is made to flow.

13. The liquid phase growth apparatus according  
to Claim 10, wherein the cooling section is a hole  
10 which is formed in the crucible and through which a  
medium is made to flow.

14. The liquid phase growth apparatus according  
to Claim 11, wherein the medium is a gas.

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16. The liquid phase growth apparatus according  
to Claim 14, wherein the gas is hydrogen or nitrogen  
gas as an atmospheric gas.

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17. The liquid phase growth apparatus according  
to Claim 10, wherein the crucible comprises a liquid  
phase growth bath for formation of a p<sup>+</sup> type Si layer  
and a liquid phase growth bath for formation of an n<sup>-</sup>  
type Si layer.

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18. The liquid phase growth apparatus according  
to Claim 10, wherein the wafer cassette is rotatable

about its own axis.

18. The liquid phase growth apparatus according  
to Claim 10, wherein the wafer cassette is revolvable  
5 about an axis different from its own axis.

19. The liquid phase growth apparatus according  
to Claim 10, wherein the growth material is Si, Ge, or  
GaAs.

10 20. The liquid phase growth apparatus according  
to Claim 10, wherein the solvent is a melt of In or Sn.